

## S72NS-N Based MCPs

Stacked Multi-Chip Product (MCP) MirrorBit™ Flash Memory & DRAM  
128 Mb (8 M x 16 bit)/256 Mb (16 M x 16 bit),  
110nm CMOS 1.8 Volt-only, Multiplexed, Simultaneous Read/Write,  
Burst Mode Flash Memory and 128/256-Mb (8/16-M x 16-bit) DDR  
DRAM



*Data Sheet*

**ADVANCE  
INFORMATION**

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# S72NS-N Based MCPs

Stacked Multi-Chip Product (MCP) MirrorBit™ Flash Memory & DRAM  
 128/256 Mb (8/16 M x 16 bit), 110nm CMOS 1.8 Volt-only,  
 Multiplexed, Simultaneous Read/Write, Burst Mode Flash Memory  
 and 128/256-Mb (8/16-M x 16-bit) DDR DRAM



Data Sheet

ADVANCE  
 INFORMATION

## General Description

This document contains information on the S72NS-N MCP product family. Refer to the S29NS-N data sheet (S29NS256/128N\_01, revision A4) for full electrical specifications of the Flash memory component. Refer to the DDR SDRAM Type 1 data sheet (revision A2) for full electrical specifications of the DDR SDRAM component. Refer to the DDR SDRAM Type 5 data sheet (revision A0) for full electrical specifications of the DDR SDRAM component

The S72NS Series is a product line of stacked Multi-Chip Product (MCP) products and consists of:

- One or more NS family multiplexed Flash memory die
- DDR DRAM

The products covered by this document are listed in the table below.

| Flash Density | DRAM Density |             |
|---------------|--------------|-------------|
|               | 128 Mb       | 256 Mb      |
| 128 Mb        | S72NS128ND0  | S72NS256ND0 |
| 256 Mb        | S72NS256ND0  |             |
| 512 Mb        | S72NS512ND0  | S72NS512NE0 |

## Distinctive Characteristics

### MCP Features

- Power supply voltage of 1.7 V to 1.95 V
- Burst Speeds
  - Flash = 66 MHz, 80 MHz
  - DRAM = 133 MHz
- Packages, 133-ball FBGA
  - 11.0 x 10.0 x 1.0 mm
  - 8.0 x 8.0 x 1.0 mm
- Operating Temperature of 25°C to +85°C

## Product Selector Guide

| Device- Model# | Flash Density | DRAM Density | Flash Speed (MHz) | DRAM Speed (MHz) | Supplier    | Package         |                |                |
|----------------|---------------|--------------|-------------------|------------------|-------------|-----------------|----------------|----------------|
| S72NS256ND0-7K | 256 Mb        | 128 Mb       | 66                | 133              | DRAM Type 1 | NLC133, 11x10mm |                |                |
| S72NS256ND0-7J |               |              | 80                |                  |             |                 |                |                |
| S72NS256ND0-73 |               |              | 66                |                  |             |                 |                |                |
| S72NS256ND0-72 |               |              | 80                |                  |             |                 |                |                |
| S72NS128ND0-1K | 128 Mb        | 128 Mb       | 66                |                  | 133         | DRAM Type 1     | NLE133, 8x8mm  |                |
| S72NS128ND0-1J |               |              | 80                |                  |             |                 |                |                |
| S72NS128ND0-13 |               |              | 66                |                  |             |                 |                |                |
| S72NS128ND0-12 |               |              | 80                |                  |             |                 |                |                |
| S72NS512ND0-7K | 512 Mb        | 128 Mb       | 66                | 133              |             | DRAM Type 1     | MTA133 11x10mm |                |
| S72NS512ND0-7J |               |              | 80                |                  |             |                 |                |                |
| S72NS512ND0-73 |               |              | 66                |                  |             |                 |                |                |
| S72NS512ND0-72 |               |              | 80                |                  |             |                 |                |                |
| S72NS512NE0-7K | 512 Mb        | 256 Mb       | 66                |                  | 133         | DRAM Type 1     |                | MTA133 11x10mm |
| S72NS512NE0-7J |               |              | 80                |                  |             |                 |                |                |
| S72NS512NE0-73 |               |              | 66                |                  |             |                 |                |                |
| S72NS512NE0-72 |               |              | 80                |                  |             |                 |                |                |

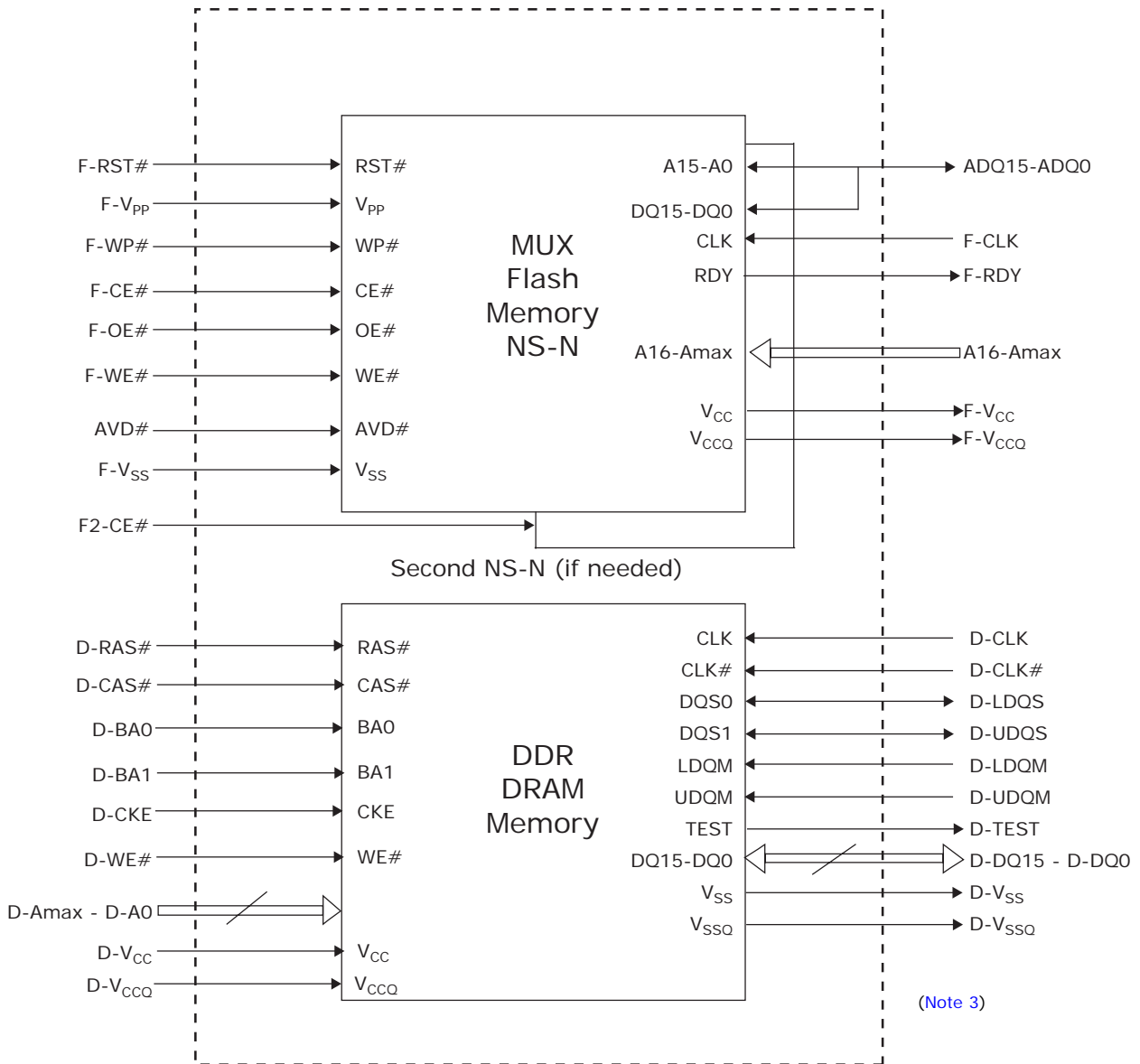
Publication Number S72NSI28\_256ND0\_00 Revision B Amendment I Issue Date November 9, 2005

This document contains information on one or more products under development at Spansion LLC. The information is intended to help you evaluate this product. Do not design in this product without contacting the factory. Spansion LLC reserves the right to change or discontinue work on this proposed product without notice.

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# I MCP Block Diagrams



**Notes:**

- Amax indicates highest address bit for memory component:
  - Amax = A23 for NS256N, A22 for NS128N
  - Amax = A11 for 128 Mb DDR DRAM, A12 for 256-Mb DDR DRAM
- For Flash, A0 – A15 is tied to DQ0 – DQ15.
- For the NS512N, two NS-N devices are included. All signals are common to both except for CE#. F-CE# becomes F1-CE#, while the CE# for the second flash is F2-CE#. This way, the two NS-N devices are separately accessed.

**Figure I.I. MCP Block Diagram**

## 2 Connection Diagrams

### 2.1 256 Mb Flash + I28 Mb DDR SDRAM Pinout

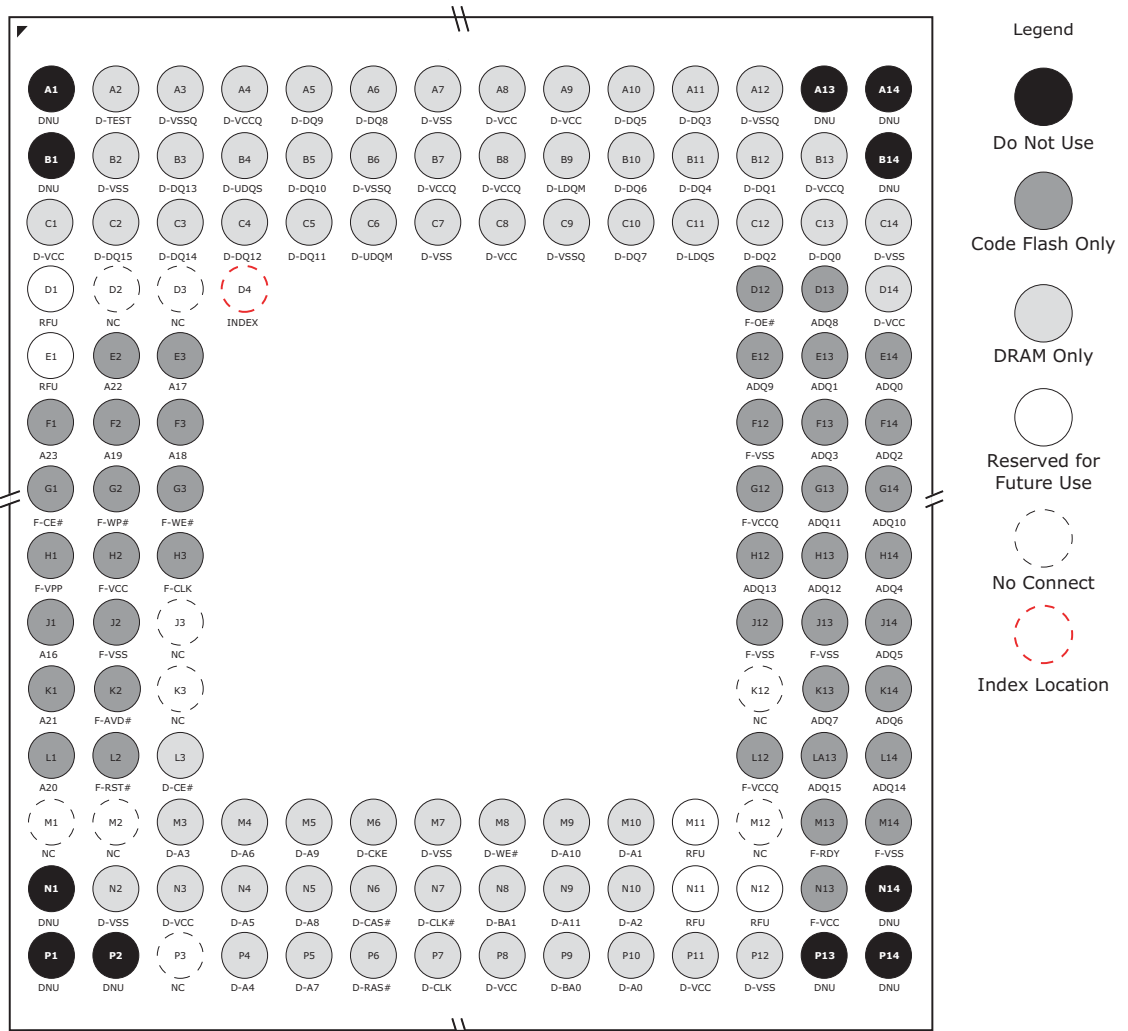


Figure 2.1. 133-ball Fine-Pitch Ball Grid Array, 256 Mb Flash + I28 Mb DDR DRAM

## 2.2 512 Mb Flash + I28 Mb DDR SDRAM Pinout

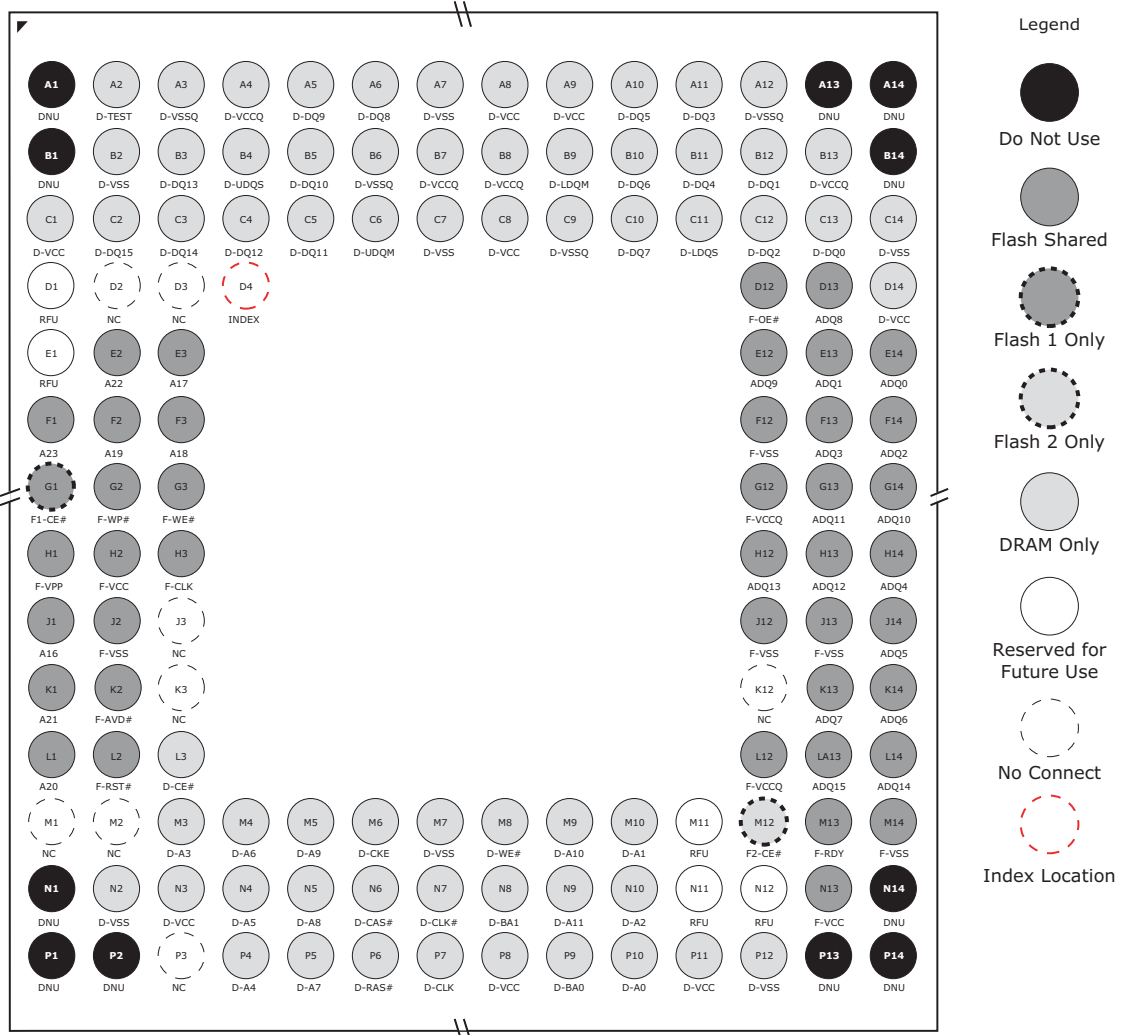
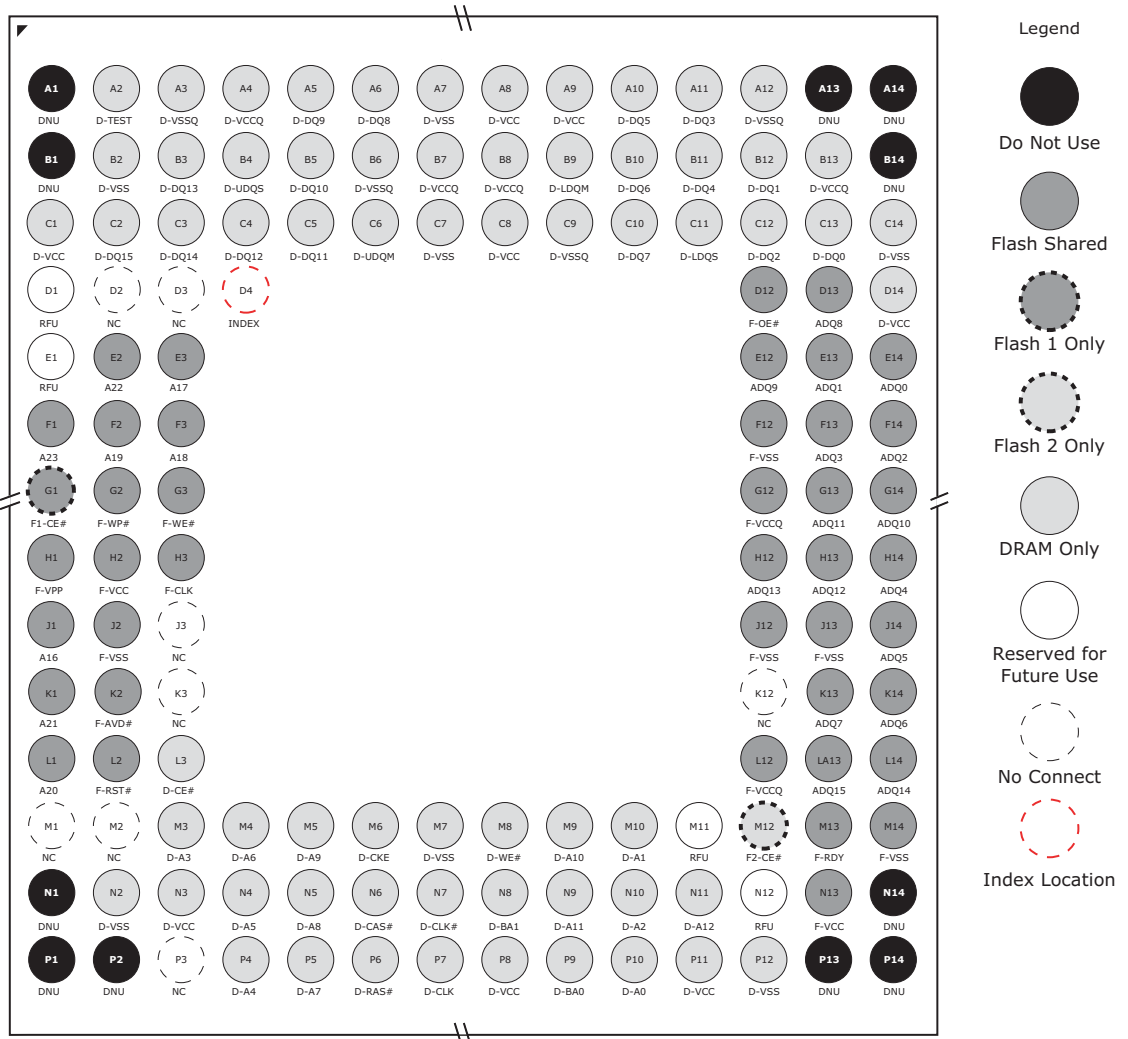


Figure 2.2. I33-ball Fine-Pitch Ball Grid Array, 512 Mb Flash + I28 Mb DDR DRAM

### 2.3 512 Mb Flash + 256 Mb DDR SDRAM Pinout



**Figure 2.3. 133-ball Fine-Pitch Ball Grid Array, 512 Mb Flash + 256 Mb DDR DRAM**



## 2.4 128 Mb Flash + 128 Mb DDR SDRAM Pinout

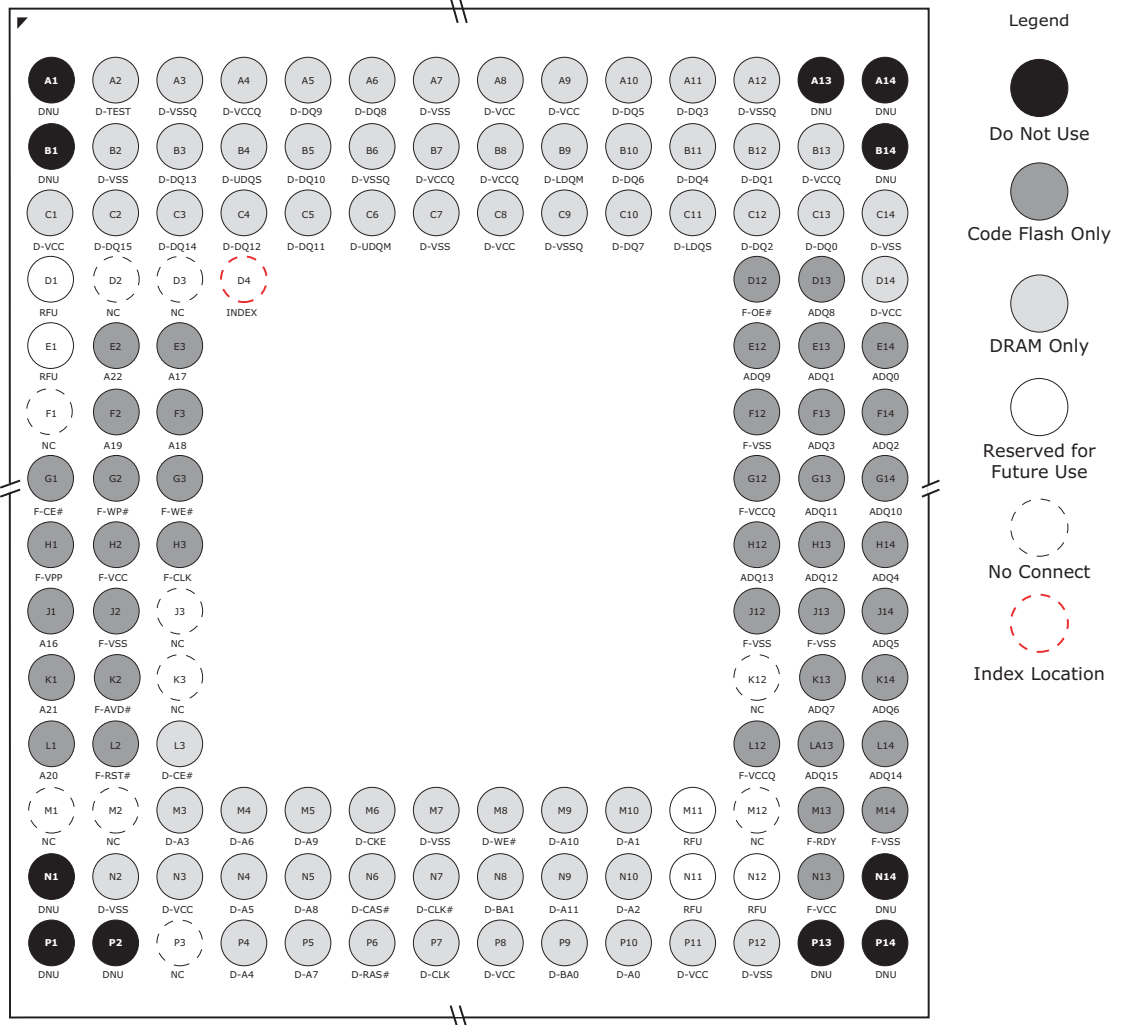


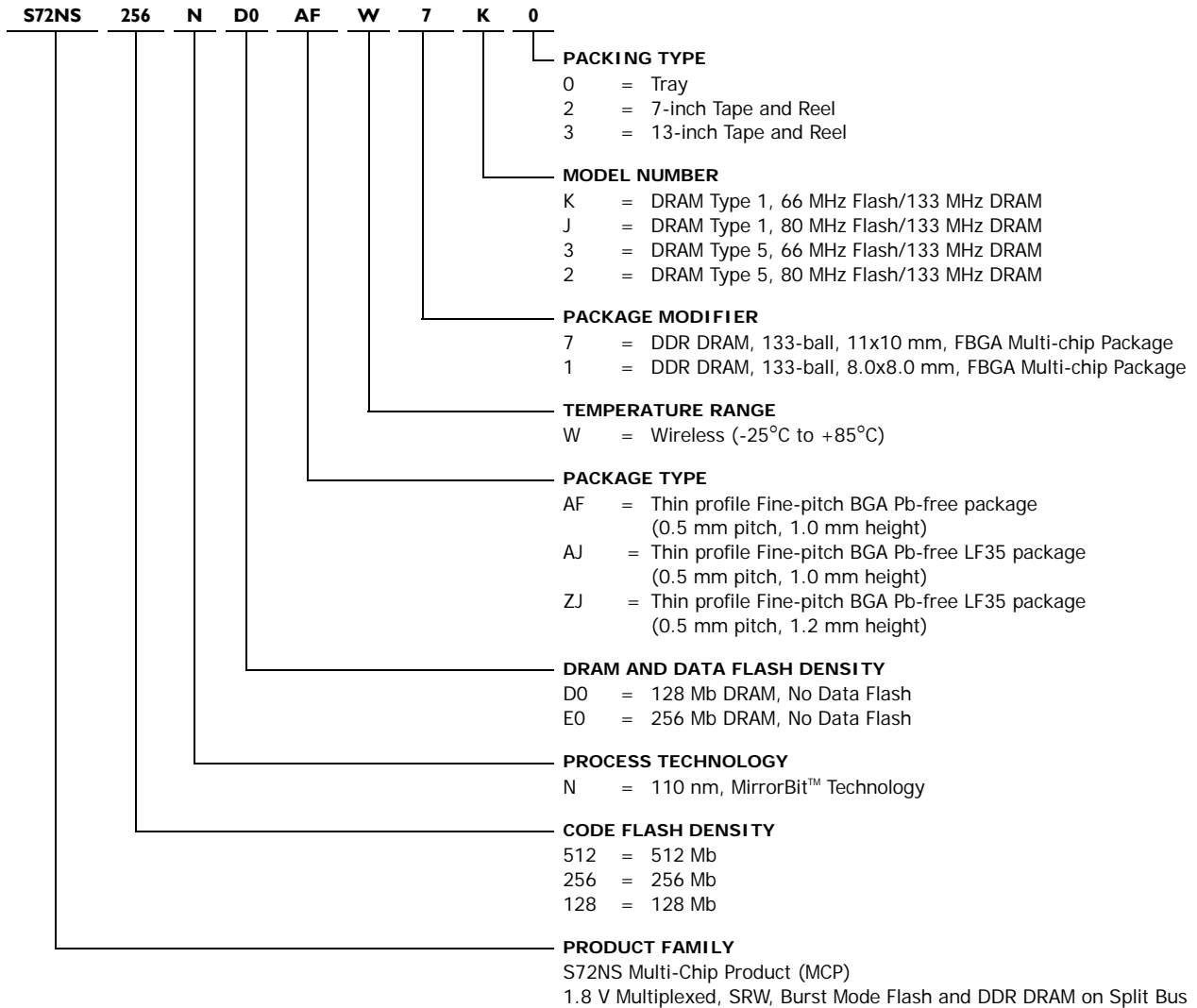
Figure 2.4. 133-ball Fine-Pitch Ball Grid Array, 128 Mb Flash + 128 Mb DDR DRAM

### 3 Input/Output Descriptions

|                    |   |  |
|--------------------|---|--|
| A23 – A0           | = | Flash Address inputs   |
| DQ15 – DQ0         | = | Flash Data input/output  |
| F-CE#              | = | Flash Chip-enable input. Asynchronous relative to CLK for Burst Mode   |
| F-OE#              | = | Flash Output Enable input. Asynchronous relative to CLK for Burst mode.  |
| F-WE#              | = | Flash Write Enable input   |
| F-V <sub>CC</sub>  | = | Flash device power supply (1.7 V to 1.95 V)  |
| F-V <sub>CCQ</sub> | = | Flash Input/Output Buffer power supply   |
| F-V <sub>SS</sub>  | = | Flash Ground   |
| F-RDY              | = | Flash ready output. Indicates the status of the Burst read. V <sub>OL</sub> = data invalid. V <sub>OH</sub> = data valid.  |
| F-CLK              | = | Flash Clock. The first rising edge of CLK in conjunction with AVD# low latches the address input and activates burst mode operation. After the initial word is output, subsequent rising edges of CLK increment the internal address counter. CLK should remain low during asynchronous access.        |
| F-AVD#             | = | Flash Address Valid input. Indicates to device that the valid address is present on the address inputs. V <sub>IL</sub> = for asynchronous mode, indicates valid address; for burst mode, causes starting address to be latched on rising edge of CLK. V <sub>IH</sub> = device ignores address inputs |
| F-RST#             | = | Flash hardware reset input. V <sub>IL</sub> = device resets and returns to reading array data  |
| F-WP#              | = | Flash hardware write protect input. V <sub>IL</sub> = disables program and erase functions in the four outermost sectors   |
| F-V <sub>PP</sub>  | = | Flash accelerated input. At V <sub>IH</sub> , accelerates programming; automatically places device in unlock bypass mode. At V <sub>IL</sub> , disables all program and erase functions. Should be at V <sub>IH</sub> for all other conditions.  |
| D-A11 – D-A0       | = | DRAM Address inputs.   |
| D-DQ15 – D-DQ0     | = | DRAM Data input/output   |
| D-CLK              | = | DRAM System Clock  |
| D-CE#              | = | DRAM Chip Select   |
| D-CKE              | = | DRAM Clock Enable  |
| D-BA1 – BA0        | = | DRAM Bank Select   |
| D-RAS#             | = | DRAM Row Address Strobe  |
| D-CAS#             | = | DRAM Column Address Strobe   |
| D-DM1 – D-DM0      | = | DRAM Data Input/Output Mask  |
| D-WE#              | = | DRAM Write Enable input  |
| D-V <sub>SS</sub>  | = | DRAM Ground  |
| D-V <sub>SSQ</sub> | = | DRAM Input/Output Buffer ground  |
| D-V <sub>CCQ</sub> | = | DRAM Input/Output Buffer power supply  |
| D-V <sub>CC</sub>  | = | DRAM device power supply   |
| D-UDQS             | = | DRAM Upper Data Strobe, output with read data and input with write data  |
| D-LDQS             | = | DRAM Lower Data Strobe, output with read data and input with write data  |
| D-CLK#             | = | DDR Clock for negative edge of CLK   |
| RFU                | = | Reserved for Future Use  |
| NC                 | = | No Connect. Can be connected to ground or left floating.   |
| D-TEST             | = | Internal Test mode pin for DDR DRAM only. Do not apply any signal on this pin. Can be connected to ground or left floating.  |

## 4 Ordering Information

The order number (Valid Combination) is formed by the following:



| Valid Combinations |                         |                    |                   |                                 |                   |                  |              |              |
|--------------------|-------------------------|--------------------|-------------------|---------------------------------|-------------------|------------------|--------------|--------------|
| Product Family     | Code Flash Density (Mb) | Process Technology | DRAM Density (Mb) | Package Type/ Marking/ Material | Temperature Range | Package Modifier | Model Number | Packing Type |
| S72NS              | 128                     | N                  | D0                | AF, AJ                          | W                 | 1                | K, J, 2, 3   | 0, 2, 3      |
|                    | 256                     |                    |                   |                                 |                   | 7                |              |              |
|                    | 512                     |                    | E0                | ZJ                              |                   |                  |              |              |

**Notes:**

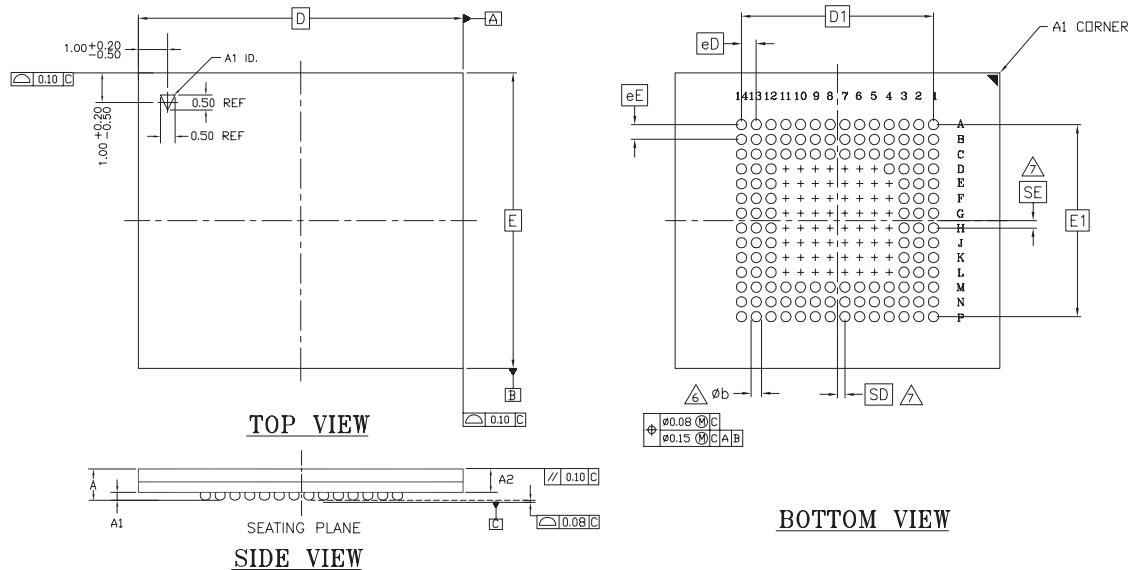
- Packing Type 0 is standard. Specify other options as required.
- BGA package marking omits leading "S" and packing type designator from ordering part number.

**Valid Combinations**

Valid Combinations list configurations planned to be supported in volume for this device. Consult your local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

## 5 Physical Dimensions

### 5.1 NLC133—133-ball Fine-Pitch Ball Grid Array (FBGA) 11.0 x 10.0 x 1.0 mm MCP Package



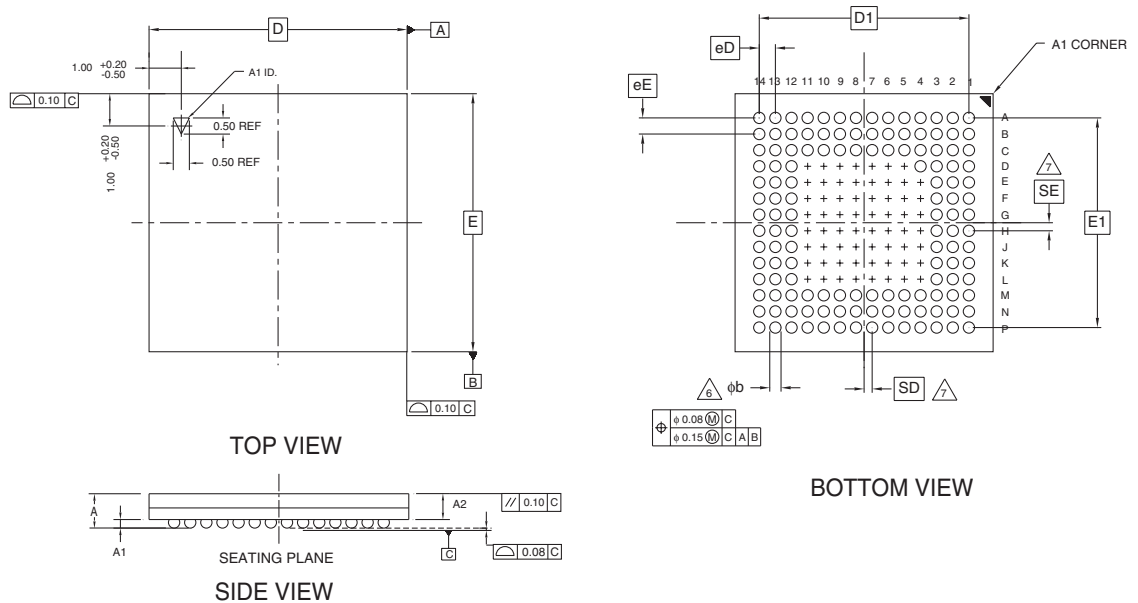
| PACKAGE | NLC 133  |      |      | NOTE                     |
|---------|--|------|------|--------------------------|
| JEDEC   | N/A  |      |      |                          |
| D x E   | 11.0 mm x 10.0 mm PACKAGE  |      |      |                          |
| SYMBOL  | MIN  | NOM  | MAX  |                          |
| A       | 0.90   | 1.00 | 1.10 | PROFILE                  |
| A1      | 0.20   | 0.25 | 0.30 | BALL HEIGHT              |
| A2      | 0.70   | 0.76 | 0.82 | BODY THICKNESS           |
| D       | 10.9   | 11.0 | 11.1 | BODY SIZE                |
| E       | 9.9  | 10.0 | 10.1 | BODY SIZE                |
| D1      | 6.50 BSC.  |      |      | MATRIX FOOTPRINT         |
| E1      | 6.50 BSC.  |      |      | MATRIX FOOTPRINT         |
| MD      | 14   |      |      | MATRIX SIZE D DIRECTION  |
| ME      | 14   |      |      | MATRIX SIZE E DIRECTION  |
| n       | 133  |      |      | BALL COUNT               |
| Øb      | 0.25   | 0.30 | 0.35 | BALL DIAMETER            |
| eE      | 0.50 BSC.  |      |      | BALL PITCH               |
| eD      | 0.50 BSC.  |      |      | BALL PITCH               |
| SD / SE | 0.25 BSC.  |      |      | SOLDER BALL PLACEMENT    |
|         | D5-D11, E4-E11, F4-F11<br>G4-G11, H4-H11, J4-J11<br>K4-K11, L4-L11 |      |      | DEPOPULATED SOLDER BALLS |

NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
- [e] REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.  
SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.  
n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
- WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.  
WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = [e/2]
- "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
- N/A
- A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

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## 5.2 NLEI33—I33-ball Fine-Pitch Ball Grid Array (FBGA) 8.0 x 8.0 x 1.0 mm MCP Package



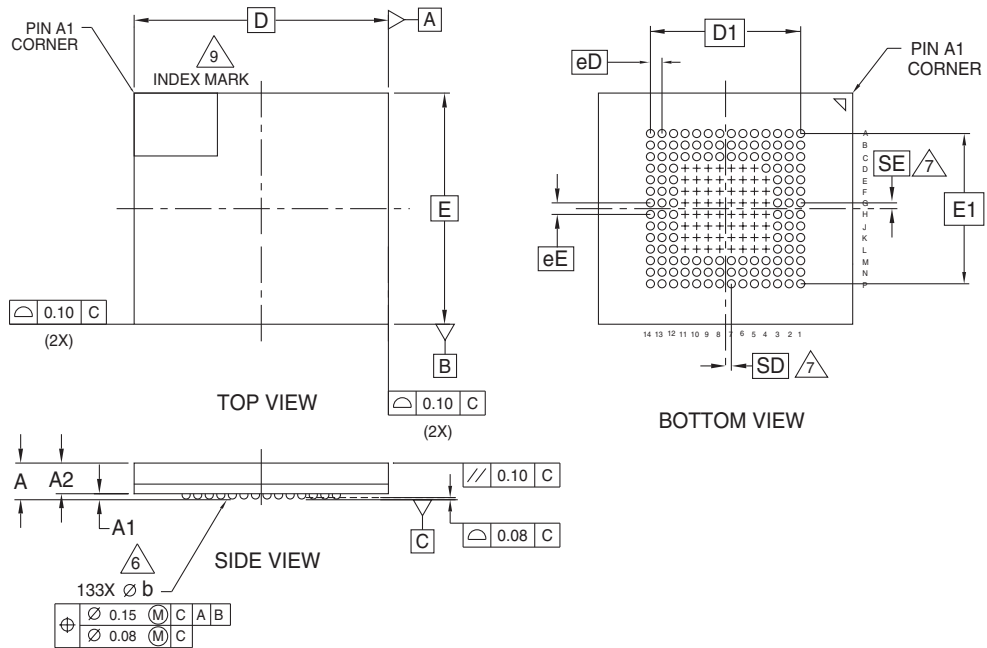
| PACKAGE  | NLE 133  |      |      | NOTE                     |
|----------|--|------|------|--------------------------|
| JEDEC    | N/A  |      |      |                          |
| D x E    | 8.00 mm x 8.00 mm PACKAGE  |      |      |                          |
| SYMBOL   | MIN  | NOM  | MAX  |                          |
| A        | 0.90   | 1.00 | 1.10 | PROFILE                  |
| A1       | 0.20   | 0.25 | 0.30 | BALL HEIGHT              |
| A2       | 0.70   | 0.76 | 0.82 | BODY THICKNESS           |
| D        | 7.90   | 8.00 | 8.10 | BODY SIZE                |
| E        | 7.90   | 8.00 | 8.10 | BODY SIZE                |
| D1       | 6.50 BSC.  |      |      | MATRIX FOOTPRINT         |
| E1       | 6.50 BSC.  |      |      | MATRIX FOOTPRINT         |
| MD       | 14   |      |      | MATRIX SIZE D DIRECTION  |
| ME       | 14   |      |      | MATRIX SIZE E DIRECTION  |
| n        | 133  |      |      | BALL COUNT               |
| $\phi b$ | 0.25   | 0.30 | 0.35 | BALL DIAMETER            |
| eE       | 0.50 BSC.  |      |      | BALL PITCH               |
| eD       | 0.50 BSC.  |      |      | BALL PITCH               |
| SD / SE  | 0.25 BSC.  |      |      | SOLDER BALL PLACEMENT    |
|          | D5-D11, E4-E11, F4-F11, G4-G11<br>H4-H11, J4-J11, K4-K11, L4-L11 |      |      | DEPOPULATED SOLDER BALLS |

NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JESD 95-1 SPP-010.
- $\square e$  REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.  
SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.  
n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- $\triangle b$  DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- $\triangle$  SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.  
WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.  
WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE =  $\lfloor e/2 \rfloor$
- "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
- $\triangle$  A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

3513 \ 16-038.22 \ 08.09.05

### 5.3 MTA133—I33-ball Fine-Pitch Ball Grid Array (FBGA) 10.0 x 11.0 x 1.0 mm MCP Package



| PACKAGE | MTA 133  |      |      | NOTE                      |
|---------|--|------|------|---------------------------|
| JEDEC   | N/A  |      |      |                           |
| D X E   | 11.00 mm x 10.00 mm PACKAGE  |      |      |                           |
| SYMBOL  | MIN  | NOM  | MAX  | NOTE                      |
| A       | ---  | ---  | 1.30 | PROFILE                   |
| A1      | 0.20   | ---  | ---  | BALL HEIGHT               |
| A2      | 0.91   | ---  | 1.06 | BODY THICKNESS            |
| D       | 11.00 BSC.   |      |      | BODY SIZE                 |
| E       | 10.00 BSC.   |      |      | BODY SIZE                 |
| D1      | 6.50 BSC.  |      |      | MATRIX FOOTPRINT          |
| E1      | 6.50 BSC.  |      |      | MATRIX FOOTPRINT          |
| MD      | 14   |      |      | MATRIX SIZE D DIRECTION   |
| ME      | 14   |      |      | MATRIX SIZE E DIRECTION   |
| n       | 133  |      |      | BALL COUNT                |
| N       | 133  |      |      | MAXIMUM NUMBER OF BALLS   |
| R       | 2  |      |      | NUMBER OF LAND PERIMETERS |
| Ø b     | 0.25   | 0.30 | 0.35 | BALL DIAMETER             |
| eE      | 0.50 BSC.  |      |      | BALL PITCH                |
| eD      | 0.50 BSC.  |      |      | BALL PITCH                |
| SE SD   | 0.25 BSC.  |      |      | SOLDER BALL PLACEMENT     |
|         | 4L ~ 4E, 5L ~ 5D, 6L ~ 6D, 7L ~ 7D, 8L ~ 8D, 9L ~ 9D, 10L ~ 10D, 11L ~ 11D |      |      | DEPOPULATED SOLDER BALL   |

NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JEP95, SECTION 3.0, SPP-010.
- $\boxed{e}$  REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.  
SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.  
n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- $\triangle 6$  DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.  
DATUM C IS THE SEATING PLANE AND IS DEFINED BY THE CROWNS OF THE SOLDER BALLS.
- $\triangle 7$  SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.  
WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.  
WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE =  $\boxed{e}/2$
- "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
- $\triangle 9$  A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.
- OUTLINE AND DIMENSIONS PER CUSTOMER REQUIREMENT.

3529 / 16.038 / 11.08.05

## 6 Revision Summary

### MCP Revision History

#### Revision A0 (January 3, 2005)

Initial release.

#### Revision A1 (April 25, 2005)

##### Global

Updated the flash module

Updated the SDRAM Type 1 module

#### Revision A2 (May 20, 2005)

##### Global

Data sheet format modularized.

##### Distinctive Characteristics

Package description changed from 10.0 x 11.0 x 1.0 to 11.0 x 10.0 x 1.0

##### MCP Block Diagrams

Changed the F-ACC signal to F-VPP

Changed the ACC description to VPP

##### Connection Diagrams

Changed the F-ACC pin to F-VPP

##### Input/Output Descriptions

Updated description for F-RDY

Changed the F-ACC description to F-VPP

Updated description for NC and D-TEST

Product Revision Identification

New section added.

#### Revision B0 (August 15, 2005)

##### Global

Data sheet revised to include 128/128 MCP details.

##### Distinctive Characteristics

Package description changed to include new 128/128 MCP details and update the Product Selector Guide table.

##### Connection Diagrams

New 128 Mb Flash + 128 Mb DDR SDRAM Pinout added.

##### Ordering Information

New valid combinations added to the table.

##### Physical Dimensions

New illustration for 8.0 x 8.0 x 1.0 mm MCP Package added.

**Revision B1 (November 9, 2005)**

**Added DDR DRAM Type 5 Information**

Updated General Description, Product Selector Guide, Ordering Information, and Valid Combinations with DDR DRAM Type 5 Information.

**S29NS-N Flash Module**

Removed all of the Revision Summary except for A4 (request from customer).

**SDRAM (Micron) Revision Summary**

Removed all of the Revision Summary except for A1 (request from customer).

**SDRAM (Elpida) Revision Summary**

New SDRAM to be added to MCP

**S29NS-N Revision Summary**

**Revision A4 Flash Module (April 21, 2005)**

**Global Changes**

Removed all ordering options and package information listed in revision A4 of the discrete data sheet.

Removed 54 MHz speed option.

Changed ACC to  $V_{pp}$ .

**Read Access Times**

Removed burst access for 54MHz.

Defined asynchronous random access and synchronous random access to 80 ns for all speed options.

**DC Characteristics**

CMOS Compatible Table.

Updated  $I_{CC3}$  and  $I_{CC6}$  values from 40  $\mu$ A to 70  $\mu$ A.

**SDRAM Type I Revision Summary**

**Revision A2 (November 1, 2005)**

**Features**

Changed  $V_{DD}/V_{DDQ}$  range from 1.7 V-1.9 V to 1.7 V-1.95 V

Indicated temperature range (-40°C to 85°C)

**Stopping the External Clock**

Removed information that limited the rate of frequency change.

**IDD Specifications and Conditions table**

Specifications and conditions updated.

**Electrical Characteristics and Recommended AC Operating Conditions table**

Removed  $t_{REFC}$  parameter

**SDRAM Type 5 Revision Summary**

**Revision A0 (September 30, 2005)**

Initial release. New SDRAM module.



**Colophon**

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